

# Erik Janzen

## List of Publications by Citations

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624  
papers

13,486  
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58  
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632  
ext. papers

14,625  
ext. citations

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L-index

#	Paper	IF	Citations
624	Coherent control of single spins in silicon carbide at room temperature. <i>Nature Materials</i> , <b>2015</b> , 14, 164-87	27	347
623	Isolated electron spins in silicon carbide with millisecond coherence times. <i>Nature Materials</i> , <b>2015</b> , 14, 160-3	27	278
622	Deep level defects in electron-irradiated 4H SiC epitaxial layers. <i>Journal of Applied Physics</i> , <b>1997</b> , 81, 6155-6159	2.4	241
621	Accurate defect levels obtained from the HSE06 range-separated hybrid functional. <i>Physical Review B</i> , <b>2010</b> , 81,	3.3	224
620	Deep levels created by low energy electron irradiation in 4H-SiC. <i>Journal of Applied Physics</i> , <b>2004</b> , 96, 4909-4915	2.5	215
619	High-resolution studies of sulfur- and selenium-related donor centers in silicon. <i>Physical Review B</i> , <b>1984</b> , 29, 1907-1918	3.3	209
618	Silicon vacancy related defect in 4H and 6H SiC. <i>Physical Review B</i> , <b>2000</b> , 61, 2613-2620	3.3	202
617	Electronic structure of the GaAs:MnGa center. <i>Physical Review B</i> , <b>1997</b> , 55, 6938-6944	3.3	180
616	Negative-U system of carbon vacancy in 4H-SiC. <i>Physical Review Letters</i> , <b>2012</b> , 109, 187603	7.4	176
615	Theory of spin-conserving excitation of the N-V(-) center in diamond. <i>Physical Review Letters</i> , <b>2009</b> , 103, 186404	7.4	158
614	Divacancy in 4H-SiC. <i>Physical Review Letters</i> , <b>2006</b> , 96, 055501	7.4	151
613	Influence of epitaxial growth and substrate-induced defects on the breakdown of 4H-SiC Schottky diodes. <i>Applied Physics Letters</i> , <b>2000</b> , 76, 2725-2727	3.4	144
612	Electrically active defects in n-type 4H-SiC grown in a vertical hot-wall reactor. <i>Journal of Applied Physics</i> , <b>2003</b> , 93, 4708-4714	2.5	141
611	Photoluminescence studies of porous silicon carbide. <i>Applied Physics Letters</i> , <b>1995</b> , 66, 2250-2252	3.4	124
610	Tellurium donors in silicon. <i>Physical Review B</i> , <b>1981</b> , 24, 4571-4586	3.3	123
609	Growth of SiC by Hot-Wall CVD and HTCVD. <i>Physica Status Solidi (B): Basic Research</i> , <b>1997</b> , 202, 321-334	1.3	115
608	Removal of polishing-induced damage from 6H-SiC(0001) substrates by hydrogen etching. <i>Journal of Crystal Growth</i> , <b>1996</b> , 167, 391-395	1.6	109

607	A 4.5 kV 6H silicon carbide rectifier. <i>Applied Physics Letters</i> , <b>1995</b> , 67, 1561-1563	3.4	103
606	In situ substrate preparation for high-quality SiC chemical vapour deposition. <i>Journal of Crystal Growth</i> , <b>1997</b> , 181, 241-253	1.6	102
605	High temperature chemical vapor deposition of SiC. <i>Applied Physics Letters</i> , <b>1996</b> , 69, 1456-1458	3.4	101
604	Ab initio density-functional supercell calculations of hydrogen defects in cubic SiC. <i>Physical Review B</i> , <b>2001</b> , 63,	3.3	99
603	Luminescence from stacking faults in 4H SiC. <i>Applied Physics Letters</i> , <b>2001</b> , 79, 3944-3946	3.4	98
602	Aggregation of carbon interstitials in silicon carbide: A theoretical study. <i>Physical Review B</i> , <b>2003</b> , 68,	3.3	94
601	Carbon vacancy-related defect in 4H and 6H SiC. <i>Physical Review B</i> , <b>2001</b> , 63,	3.3	93
600	Electrical properties and formation mechanism of porous silicon carbide. <i>Applied Physics Letters</i> , <b>1994</b> , 65, 2699-2701	3.4	93
599	Electron effective masses in 4H SiC. <i>Applied Physics Letters</i> , <b>1995</b> , 66, 1074-1076	3.4	89
598	Deep sulfur-related centers in silicon. <i>Journal of Applied Physics</i> , <b>1980</b> , 51, 4212-4217	2.5	89
597	Dislocation evolution in 4H-SiC epitaxial layers. <i>Journal of Applied Physics</i> , <b>2002</b> , 91, 6354	2.5	87
596	Scalable Quantum Photonics with Single Color Centers in Silicon Carbide. <i>Nano Letters</i> , <b>2017</b> , 17, 1782-1786	2.5	85
595	Electronic properties of selenium-doped silicon. <i>Journal of Applied Physics</i> , <b>1980</b> , 51, 3740-3745	2.5	85
594	Investigation of the interface between silicon nitride passivations and AlGaN/AlN/GaN heterostructures by C(V) characterization of metal-insulator-semiconductor-heterostructure capacitors. <i>Journal of Applied Physics</i> , <b>2010</b> , 108, 014508	2.5	84
593	Pseudodonor nature of the DI defect in 4H-SiC. <i>Applied Physics Letters</i> , <b>2001</b> , 78, 46-48	3.4	83
592	Chloride-based CVD growth of silicon carbide for electronic applications. <i>Chemical Reviews</i> , <b>2012</b> , 112, 2434-53	68.1	80
591	Properties and origins of different stacking faults that cause degradation in SiC PiN diodes. <i>Journal of Applied Physics</i> , <b>2004</b> , 95, 1485-1488	2.5	80
590	Nitrogen doping concentration as determined by photoluminescence in 4H and 6H SiC. <i>Journal of Applied Physics</i> , <b>1996</b> , 80, 3504-3508	2.5	80

589	Isolated Spin Qubits in SiC with a High-Fidelity Infrared Spin-to-Photon Interface. <i>Physical Review X</i> , <b>2017</b> , 7,	9.1	78
588	Growth rate predictions of chemical vapor deposited silicon carbide epitaxial layers. <i>Journal of Crystal Growth</i> , <b>2002</b> , 243, 170-184	1.6	75
587	Very high growth rate of 4H-SiC epilayers using the chlorinated precursor methyltrichlorosilane (MTS). <i>Journal of Crystal Growth</i> , <b>2007</b> , 307, 334-340	1.6	73
586	Properties of the D1 bound exciton in 4H-SiC. <i>Physical Review B</i> , <b>1999</b> , 59, 1956-1963	3.3	72
585	Structural macro-defects in 6H-SiC wafers. <i>Journal of Crystal Growth</i> , <b>1993</b> , 132, 504-512	1.6	72
584	The silicon vacancy in SiC. <i>Physica B: Condensed Matter</i> , <b>2009</b> , 404, 4354-4358	2.8	70
583	High temperature CVD growth of SiC. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , <b>1999</b> , 61-62, 113-120	3.1	69
582	Growth of 6H and 4H-SiC by sublimation epitaxy. <i>Journal of Crystal Growth</i> , <b>1999</b> , 197, 155-162	1.6	69
581	Impact of residual carbon on two-dimensional electron gas properties in Al <sub>x</sub> Ga <sub>1-x</sub> N/GaN heterostructure. <i>Applied Physics Letters</i> , <b>2013</b> , 102, 193506	3.4	68
580	Identification of the carbon antisite-vacancy pair in 4H-SiC. <i>Physical Review Letters</i> , <b>2006</b> , 96, 145501	7.4	66
579	Correlation between the antisite pair and the DI center in SiC. <i>Physical Review B</i> , <b>2003</b> , 67,	3.3	66
578	A 3 kV Schottky barrier diode in 4H-SiC. <i>Applied Physics Letters</i> , <b>1998</b> , 72, 445-447	3.4	66
577	Thick Silicon Carbide Homoepitaxial Layers Grown by CVD Techniques. <i>Chemical Vapor Deposition</i> , <b>2006</b> , 12, 475-482		65
576	Electronic structure of the neutral silicon vacancy in 4H and 6H SiC. <i>Physical Review B</i> , <b>2000</b> , 62, 16555-16560		65
575	Electron effective masses and mobilities in high-purity 6H-SiC chemical vapor deposition layers. <i>Applied Physics Letters</i> , <b>1994</b> , 65, 3209-3211	3.4	65
574	Multivalley spin splitting of 1s states for sulfur, selenium, and tellurium donors in silicon. <i>Physical Review B</i> , <b>1982</b> , 25, 2627-2632	3.3	65
573	Techniques for Minimizing the Basal Plane Dislocation Density in SiC Epilayers to Reduce V <sub>f</sub> Drift in SiC Bipolar Power Devices. <i>Materials Science Forum</i> , <b>2006</b> , 527-529, 141-146	0.4	64
572	Fast chemical sensing with metal-insulator silicon carbide structures. <i>IEEE Electron Device Letters</i> , <b>1997</b> , 18, 287-289	4.4	62

571	Liquid phase epitaxial growth of SiC. <i>Journal of Crystal Growth</i> , <b>1999</b> , 197, 147-154	1.6	62
570	Photoexcitation-electron-paramagnetic-resonance studies of the carbon vacancy in 4H-SiC. <i>Applied Physics Letters</i> , <b>2002</b> , 81, 3945-3947	3.4	60
569	Structural defects in electrically degraded 4H-SiC p+/n <sup>-</sup> /n <sup>+</sup> diodes. <i>Applied Physics Letters</i> , <b>2002</b> , 80, 4852-4854	3.4	60
568	Determination of the electron effective-mass tensor in 4H SiC. <i>Physical Review B</i> , <b>1996</b> , 53, 15409-15412	3.3	60
567	The minority carrier lifetime of n-type 4H- and 6H-SiC epitaxial layers. <i>Applied Physics Letters</i> , <b>1996</b> , 69, 679-681	3.4	60
566	Nitrogen doping of epitaxial silicon carbide. <i>Journal of Crystal Growth</i> , <b>2002</b> , 236, 101-112	1.6	58
565	Direct generation of linearly polarized photon emission with designated orientations from site-controlled InGaN quantum dots. <i>Light: Science and Applications</i> , <b>2014</b> , 3, e139-e139	16.7	57
564	Photoluminescence of electron-irradiated 4H-SiC. <i>Physical Review B</i> , <b>1999</b> , 59, 8008-8014	3.3	57
563	EPR identification of intrinsic defects in SiC. <i>Physica Status Solidi (B): Basic Research</i> , <b>2008</b> , 245, 1298-1314	4.3	56
562	Defects and carrier compensation in semi-insulating 4H-SiC substrates. <i>Physical Review B</i> , <b>2007</b> , 75,	3.3	56
561	On-axis homoepitaxial growth on Si-face 4H-SiC substrates. <i>Journal of Crystal Growth</i> , <b>2008</b> , 310, 4424-4429	4.3	55
560	EPR and theoretical studies of negatively charged carbon vacancy in 4H-SiC. <i>Physical Review B</i> , <b>2005</b> , 71,	3.3	53
559	Current status and advances in the growth of SiC. <i>Diamond and Related Materials</i> , <b>2000</b> , 9, 432-438	3.5	53
558	Vector Magnetometry Using Silicon Vacancies in 4H-SiC Under Ambient Conditions. <i>Physical Review Applied</i> , <b>2016</b> , 6,	4.3	52
557	Time Resolved Spectroscopy of Defects in SiC. <i>Physica Status Solidi A</i> , <b>1997</b> , 162, 65-77		51
556	Aluminum doping of epitaxial silicon carbide. <i>Journal of Crystal Growth</i> , <b>2003</b> , 253, 340-350	1.6	51
555	Defects in High-Purity Semi-Insulating SiC. <i>Materials Science Forum</i> , <b>2004</b> , 457-460, 437-442	0.4	51
554	SiC Crystal Growth by HTCVD. <i>Materials Science Forum</i> , <b>2004</b> , 457-460, 9-14	0.4	51

553	Fano resonances in chalcogen-doped silicon. <i>Physical Review B</i> , <b>1985</b> , 31, 8000-8012	3.3	51
552	Reducing Thermal Resistance of AlGaN/GaN Electronic Devices Using Novel Nucleation Layers. <i>IEEE Electron Device Letters</i> , <b>2009</b> , 30, 103-106	4.4	50
551	Polytype stability in seeded sublimation growth of 4H $\beta$ SiC boules. <i>Journal of Crystal Growth</i> , <b>2000</b> , 217, 255-262	1.6	50
550	Capture cross sections of electron irradiation induced defects in 6H $\beta$ SiC. <i>Journal of Applied Physics</i> , <b>1998</b> , 84, 704-708	2.5	49
549	Effective mass of electron in monolayer graphene: Electron-phonon interaction. <i>Journal of Applied Physics</i> , <b>2013</b> , 113, 043708	2.5	48
548	Single excitons in InGaN quantum dots on GaN pyramid arrays. <i>Nano Letters</i> , <b>2011</b> , 11, 2415-8	11.5	48
547	Growth of 3CSiC on on-axis Si(100) substrates by chemical vapor deposition. <i>Journal of Crystal Growth</i> , <b>1995</b> , 154, 303-314	1.6	48
546	Theoretical model of dynamic spin polarization of nuclei coupled to paramagnetic point defects in diamond and silicon carbide. <i>Physical Review B</i> , <b>2015</b> , 92,	3.3	47
545	HTCVD Grown Semi-Insulating SiC Substrates. <i>Materials Science Forum</i> , <b>2003</b> , 433-436, 33-38	0.4	47
544	Doping-induced strain in N-doped 4H $\beta$ SiC crystals. <i>Applied Physics Letters</i> , <b>2003</b> , 82, 3689-3691	3.4	47
543	Layer-number determination in graphene on SiC by reflectance mapping. <i>Carbon</i> , <b>2014</b> , 77, 492-500	10.4	46
542	Step-bunching in SiC epitaxy: anisotropy and influence of growth temperature. <i>Journal of Crystal Growth</i> , <b>2002</b> , 236, 297-304	1.6	46
541	High quality 4H-SiC epitaxial layers grown by chemical vapor deposition. <i>Applied Physics Letters</i> , <b>1995</b> , 66, 1373-1375	3.4	45
540	Investigation on origin of Z1/2 center in SiC by deep level transient spectroscopy and electron paramagnetic resonance. <i>Applied Physics Letters</i> , <b>2013</b> , 102, 112106	3.4	44
539	Epitaxial growth of SiC in a chimney CVD reactor. <i>Journal of Crystal Growth</i> , <b>2002</b> , 236, 225-238	1.6	44
538	High-quality AlN layers grown by hot-wall MOCVD at reduced temperatures. <i>Journal of Crystal Growth</i> , <b>2012</b> , 338, 52-56	1.6	43
537	EPR and theoretical studies of positively charged carbon vacancy in 4H $\beta$ SiC. <i>Physical Review B</i> , <b>2004</b> , 70,	3.3	43
536	Crystalline imperfections in 4H SiC grown with a seeded Lely method. <i>Journal of Crystal Growth</i> , <b>1994</b> , 144, 267-276	1.6	43

535	Resonant optical spectroscopy and coherent control of Cr <sup>4+</sup> spin ensembles in SiC and GaN. <i>Physical Review B</i> , <b>2017</b> , 95,	3-3	42
534	Spin and photophysics of carbon-antisite vacancy defect in 4H silicon carbide: A potential quantum bit. <i>Physical Review B</i> , <b>2015</b> , 91,	3-3	41
533	Stable and metastable Si negative-U centers in AlGa <sub>x</sub> N and AlN. <i>Applied Physics Letters</i> , <b>2014</b> , 105, 162106.	3-4	41
532	Shallow donor and DX states of Si in AlN. <i>Applied Physics Letters</i> , <b>2011</b> , 98, 092104	3-4	41
531	Dispersive Effects in Microwave AlGa <sub>x</sub> N/AlN/GaN HEMTs With Carbon-Doped Buffer. <i>IEEE Transactions on Electron Devices</i> , <b>2015</b> , 62, 2162-2169	2-9	40
530	Identification of the gallium vacancy-oxygen pair defect in GaN. <i>Physical Review B</i> , <b>2009</b> , 80,	3-3	40
529	Improved morphology for epitaxial growth on 4° off-axis 4H-SiC substrates. <i>Journal of Crystal Growth</i> , <b>2009</b> , 311, 3265-3272	1-6	40
528	Hot-Wall MOCVD for Highly Efficient and Uniform Growth of AlN. <i>Crystal Growth and Design</i> , <b>2009</b> , 9, 880-884	3-5	40
527	Negative-U carbon vacancy in 4H-SiC: Assessment of charge correction schemes and identification of the negative carbon vacancy at the quasicubic site. <i>Physical Review B</i> , <b>2013</b> , 88,	3-3	39
526	Optical Characterization of Deep Level Defects in SiC. <i>Materials Science Forum</i> , <b>2005</b> , 483-485, 341-346	0-4	39
525	Ligand hyperfine interaction at the neutral silicon vacancy in 4H- and 6H-SiC. <i>Physical Review B</i> , <b>2002</b> , 66,	3-3	39
524	Direct observation of intercenter charge transfer in dominant nonradiative recombination channels in silicon. <i>Physical Review Letters</i> , <b>1991</b> , 67, 1914-1917	7-4	39
523	In-situ surface preparation of nominally on-axis 4H-SiC substrates. <i>Journal of Crystal Growth</i> , <b>2008</b> , 310, 4430-4437	1-6	38
522	Characterisation and Defects in Silicon Carbide. <i>Materials Science Forum</i> , <b>2002</b> , 389-393, 9-14	0-4	38
521	Growth of high-quality 3C-SiC epitaxial films on off-axis Si(001) substrates at 850 °C by reactive magnetron sputtering. <i>Applied Physics Letters</i> , <b>1994</b> , 65, 725-727	3-4	38
520	Intrinsic Defects in Silicon Carbide Polytypes. <i>Materials Science Forum</i> , <b>2001</b> , 353-356, 499-504	0-4	37
519	Observation of rapid direct charge transfer between deep defects in silicon. <i>Physical Review Letters</i> , <b>1994</b> , 72, 2939-2942	7-4	37
518	Theoretical unification of hybrid-DFT and DFT + U methods for the treatment of localized orbitals. <i>Physical Review B</i> , <b>2014</b> , 90,	3-3	36

517	Improved hot-wall MOCVD growth of highly uniform AlGa <sub>N</sub> /Ga <sub>N</sub> /HEMT structures. <i>Journal of Crystal Growth</i> , <b>2009</b> , 311, 3007-3010	1.6	35
516	Interface chemistry and electric characterisation of nickel metallisation on 6H-SiC. <i>Applied Surface Science</i> , <b>1996</b> , 99, 119-125	6.7	35
515	Temperature dependent effective mass in AlGa <sub>N</sub> /Ga <sub>N</sub> high electron mobility transistor structures. <i>Applied Physics Letters</i> , <b>2012</b> , 101, 192102	3.4	34
514	Heat Capacity of 4H-SiC Determined by Differential Scanning Calorimetry. <i>Journal of the Electrochemical Society</i> , <b>2000</b> , 147, 3546	3.9	34
513	Silicon antisite in 4H SiC. <i>Physical Review Letters</i> , <b>2001</b> , 87, 045502	7.4	34
512	Electronic properties of Si-doped Al <sub>x</sub> Ga <sub>1-x</sub> N with aluminum mole fractions above 80%. <i>Journal of Applied Physics</i> , <b>2016</b> , 120, 145702	2.5	34
511	Room-temperature mobility above 2200 cm <sup>2</sup> /V <sup>1/2</sup> s of two-dimensional electron gas in a sharp-interface AlGa <sub>N</sub> /Ga <sub>N</sub> heterostructure. <i>Applied Physics Letters</i> , <b>2015</b> , 106, 251601	3.4	33
510	Quantitative comparison between Z1 <sub>2</sub> center and carbon vacancy in 4H-SiC. <i>Journal of Applied Physics</i> , <b>2014</b> , 115, 143705	2.5	33
509	Group-II acceptors in wurtzite AlN: A screened hybrid density functional study. <i>Applied Physics Letters</i> , <b>2010</b> , 96, 192110	3.4	33
508	Thick homoepitaxial layers grown on on-axis Si-face 6H- and 4H-SiC substrates with HCl addition. <i>Journal of Crystal Growth</i> , <b>2009</b> , 312, 24-32	1.6	33
507	Optically detected magnetic resonance studies of defects in electron-irradiated 3C SiC layers. <i>Physical Review B</i> , <b>1997</b> , 55, 2863-2866	3.3	33
506	The mechanism for cubic SiC formation on off-oriented substrates. <i>Journal of Crystal Growth</i> , <b>1997</b> , 178, 495-504	1.6	33
505	AlGaInN metal-organic-chemical-vapor-deposition gas-phase chemistry in hydrogen and nitrogen diluents: First-principles calculations. <i>Chemical Physics Letters</i> , <b>2006</b> , 431, 346-351	2.5	33
504	A GaN <sub>1-x</sub> Si <sub>x</sub> hybrid material for high-frequency and power electronics. <i>Applied Physics Letters</i> , <b>2018</b> , 113, 041605	3.4	32
503	Preferential etching of SiC crystals. <i>Diamond and Related Materials</i> , <b>1997</b> , 6, 1456-1458	3.5	32
502	Electrical characterization of metastable carbon clusters in SiC: A theoretical study. <i>Physical Review B</i> , <b>2006</b> , 73,	3.3	32
501	Observation of negative-U centers in 6H silicon carbide. <i>Applied Physics Letters</i> , <b>1999</b> , 74, 839-841	3.4	32
500	Time-resolved decay of the blue emission in porous silicon. <i>Applied Physics Letters</i> , <b>1994</b> , 65, 2451-2453	3.4	32



499	Chemical identification of deep energy levels in Si:Se. <i>Journal of Applied Physics</i> , <b>1980</b> , 51, 6238-6242	2.5	32
498	Direct current magnetron sputtered ZrB <sub>2</sub> thin films on 4H-SiC(0001) and Si(100). <i>Thin Solid Films</i> , <b>2014</b> , 550, 285-290	2.2	31
497	Photoluminescence and Zeeman effect in chromium-doped 4H and 6H SiC. <i>Journal of Applied Physics</i> , <b>1999</b> , 86, 4348-4353	2.5	31
496	Morphology Control of Hot-Wall MOCVD Selective Area Grown Hexagonal GaN Pyramids. <i>Crystal Growth and Design</i> , <b>2012</b> , 12, 5491-5496	3.5	30
495	The origin of 3C polytype inclusions in epitaxial layers of silicon carbide grown by chemical vapour deposition. <i>Diamond and Related Materials</i> , <b>1997</b> , 6, 1297-1300	3.5	30
494	Precursors for carbon doping of GaN in chemical vapor deposition. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , <b>2015</b> , 33, 021208	1.3	29
493	Role of screening in the density functional applied to transition-metal defects in semiconductors. <i>Physical Review B</i> , <b>2013</b> , 87,	3.3	29
492	Barrier height determination for n-type 4H-SiC schottky contacts made using various metals. <i>Journal of Electronic Materials</i> , <b>1998</b> , 27, 871-875	1.9	29
491	Growth characteristics of chloride-based SiC epitaxial growth. <i>Physica Status Solidi - Rapid Research Letters</i> , <b>2008</b> , 2, 278-280	2.5	29
490	Electron paramagnetic resonance and theoretical studies of shallow phosphorous centers in 3C-, 4H-, and 6H-SiC. <i>Physical Review B</i> , <b>2006</b> , 73,	3.3	29
489	Effect of impurity incorporation on crystallization in AlN sublimation epitaxy. <i>Journal of Applied Physics</i> , <b>2004</b> , 96, 5293-5297	2.5	29
488	Nitrogen incorporation during 4H-SiC epitaxy in a chimney CVD reactor. <i>Journal of Crystal Growth</i> , <b>2001</b> , 226, 267-276	1.6	29
487	Effect of vapor composition on polytype homogeneity of epitaxial silicon carbide. <i>Journal of Applied Physics</i> , <b>1996</b> , 80, 5704-5712	2.5	29
486	Capture, emission and recombination at a deep level via an excited state. <i>Journal of Physics C: Solid State Physics</i> , <b>1980</b> , 13, 6157-6165		29
485	The complex impact of silicon and oxygen on the n-type conductivity of high-Al-content AlGaN. <i>Applied Physics Letters</i> , <b>2013</b> , 102, 132113	3.4	28
484	Improved Ni ohmic contact on n-type 4H-SiC. <i>Journal of Electronic Materials</i> , <b>1997</b> , 26, 119-122	1.9	28
483	SiC material for high-power applications. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , <b>1997</b> , 46, 203-209	3.1	28
482	The material quality of CVD-grown SiC using different carbon precursors. <i>Journal of Crystal Growth</i> , <b>1998</b> , 183, 163-174	1.6	28

481	Defects in Semi-Insulating SiC Substrates. <i>Materials Science Forum</i> , <b>2003</b> , 433-436, 45-50	0.4	28
480	Micropipe Healing in Liquid Phase Epitaxial Growth of SiC. <i>Materials Science Forum</i> , <b>2000</b> , 338-342, 237-240		28
479	Carbon-vacancy related defects in 4H- and 6H-SiC. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , <b>1999</b> , 61-62, 202-206	3.1	28
478	Optically detected magnetic resonance studies of intrinsic defects in 6H-SiC. <i>Semiconductor Science and Technology</i> , <b>1999</b> , 14, 1141-1146	1.8	28
477	Dominant recombination center in electron-irradiated 3C SiC. <i>Journal of Applied Physics</i> , <b>1996</b> , 79, 3784-3786		28
476	Theory of Neutral Divacancy in SiC: A Defect for Spintronics. <i>Materials Science Forum</i> , <b>2010</b> , 645-648, 395-397	0.4	27
475	Material characterization need for SiC-based devices. <i>Materials Science in Semiconductor Processing</i> , <b>2001</b> , 4, 181-186	4.3	27
474	Fast SiC Epitaxial Growth in a Chimney CVD Reactor and HTCVD Crystal Growth Developments. <i>Materials Science Forum</i> , <b>2000</b> , 338-342, 131-136	0.4	27
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472	All-optical characterization of carrier lifetimes and diffusion lengths in MOCVD-, ELO-, and HVPE-grown GaN. <i>Journal of Crystal Growth</i> , <b>2007</b> , 300, 223-227	1.6	26
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469	Investigation of deep levels in bulk GaN material grown by halide vapor phase epitaxy. <i>Journal of Applied Physics</i> , <b>2013</b> , 114, 153702	2.5	25
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466	Predicted nitrogen doping concentrations in silicon carbide epitaxial layers grown by hot-wall chemical vapor deposition. <i>Journal of Crystal Growth</i> , <b>2003</b> , 250, 471-478	1.6	25
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456	Clustering of vacancy defects in high-purity semi-insulating SiC. <i>Physical Review B</i> , <b>2007</b> , 75,	3.3	24
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448	Donor incorporation in SiC epilayers grown at high growth rate with chloride-based CVD. <i>Journal of Crystal Growth</i> , <b>2009</b> , 311, 1321-1327	1.6	22
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330	Divacancy and Its Identification: Theory. <i>Materials Science Forum</i> , <b>2006</b> , 527-529, 523-526	0.4	10
329	Deep levels and carrier compensation in V-doped semi-insulating 4H-SiC. <i>Applied Physics Letters</i> , <b>2007</b> , 91, 202111	3.4	10
328	Temperature-Dependent Hall Effect Measurements in Low $\Gamma$ -Compensated p-Type 4H-SiC. <i>Materials Science Forum</i> , <b>2004</b> , 457-460, 677-680	0.4	10
327	Sublimation epitaxy of AlN on SiC: growth morphology and structural features. <i>Journal of Crystal Growth</i> , <b>2004</b> , 273, 161-166	1.6	10
326	Defects in 4H silicon carbide. <i>Physica B: Condensed Matter</i> , <b>2001</b> , 308-310, 675-679	2.8	10
325	Electronic structure of a photoluminescent center in silver-doped silicon. <i>Physical Review B</i> , <b>1994</b> , 49, 17428-17431	3.3	10
324	Metalorganic chemical vapor deposition growth of high-mobility AlGaIn/AlN/GaN heterostructures on GaN templates and native GaN substrates. <i>Journal of Applied Physics</i> , <b>2015</b> , 117, 085301	2.5	9
323	Deep level study of Mg-doped GaN using deep level transient spectroscopy and minority carrier transient spectroscopy. <i>Physical Review B</i> , <b>2016</b> , 94,	3.3	9
322	High-Resolution Raman and Luminescence Spectroscopy of Isotope-Pure $^{28}\text{Si}^{12}\text{C}$ , Natural and $^{13}\text{C}$ -Enriched 4H-SiC. <i>Materials Science Forum</i> , <b>2014</b> , 778-780, 471-474	0.4	9
321	Is the Registry Between Adjacent Graphene Layers Grown on C-Face SiC Different Compared to That on Si-Face SiC. <i>Crystals</i> , <b>2013</b> , 3, 1-13	2.3	9
320	Growth and Properties of SiC On-Axis Homoepitaxial Layers. <i>Materials Science Forum</i> , <b>2010</b> , 645-648, 83-88	0.4	9

319	Optimization of a Concentrated Chloride-Based CVD Process for 4H-SiC Epilayers. <i>Journal of the Electrochemical Society</i> , <b>2010</b> , 157, H969	3.9	9
318	Deep levels in low-energy electron-irradiated 4H-SiC. <i>Physica Status Solidi - Rapid Research Letters</i> , <b>2009</b> , 3, 121-123	2.5	9
317	EPR and ENDOR Studies of Shallow Donors in SiC. <i>Applied Magnetic Resonance</i> , <b>2010</b> , 39, 49-85	0.8	9
316	2.5 kV ion-implanted p+ n diodes in 6H-SiC. <i>Diamond and Related Materials</i> , <b>1997</b> , 6, 1485-1488	3.5	9
315	Annealing Behaviour of Vacancy-and Antisite-Related Defects in Electron-Irradiated 4H-SiC. <i>Materials Science Forum</i> , <b>2004</b> , 457-460, 473-476	0.4	9
314	Epitaxial growth of 4H SiC in a vertical hot-wall CVD reactor: Comparison between up- and down-flow orientations. <i>Journal of Crystal Growth</i> , <b>2002</b> , 241, 421-430	1.6	9
313	Possibility for the electrical activation of the carbon antisite by hydrogen in SiC. <i>Physical Review B</i> , <b>2005</b> , 71,	3.3	9
312	A Complex Defect Related to the Carbon Vacancy in 4H and 6H SiC. <i>Physica Scripta</i> , <b>1999</b> , T79, 46	2.6	9
311	On the behavior of silicon donor in conductive Al <sub>x</sub> Ga <sub>1-x</sub> N (0.63 ≤ x ≤ 1). <i>Physica Status Solidi (B): Basic Research</i> , <b>2015</b> , 252, 1306-1310	1.3	8
310	Negative-U behavior of the Si donor in Al <sub>0.77</sub> Ga <sub>0.23</sub> N. <i>Applied Physics Letters</i> , <b>2013</b> , 103, 042101	3.4	8
309	Fabrication of beam resonators from hot-wall chemical vapour deposited SiC. <i>Microelectronic Engineering</i> , <b>2009</b> , 86, 1194-1196	2.5	8
308	Defects at nitrogen site in electron-irradiated AlN. <i>Applied Physics Letters</i> , <b>2011</b> , 98, 242116	3.4	8
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306	Thermodynamic Considerations of the Role of Hydrogen in Sublimation Growth of Silicon Carbide. <i>Journal of the Electrochemical Society</i> , <b>1997</b> , 144, 1024-1027	3.9	8
305	Deep luminescent centres in electron-irradiated 6H SiC. <i>Diamond and Related Materials</i> , <b>1997</b> , 6, 1378-1389	3.9	8
304	Growth of SiC from the liquid phase: wetting and dissolution of SiC. <i>Diamond and Related Materials</i> , <b>1997</b> , 6, 1266-1268	3.5	8
303	Very high epitaxial growth rate of SiC using MTS as chloride-based precursor. <i>Surface and Coatings Technology</i> , <b>2007</b> , 201, 8931-8934	4.4	8
302	Reducing stress in silicon carbide epitaxial layers. <i>Journal of Crystal Growth</i> , <b>2003</b> , 252, 289-296	1.6	8

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300	Investigation of an Ion-Implantation Induced High Temperature Persistent Intrinsic Defect in SiC. <i>Materials Science Forum</i> , <b>2001</b> , 353-356, 377-380	0.4	8
299	Site-occupying behavior of boron in compensated p-type 4H-SiC grown by sublimation epitaxy. <i>Journal of Applied Physics</i> , <b>2002</b> , 91, 3471-3473	2.5	8
298	Behavior of Micropipes during Growth in 4H-SiC. <i>Materials Science Forum</i> , <b>2002</b> , 389-393, 395-398	0.4	8
297	The Neutral Silicon Vacancy in SiC: Ligand Hyperfine Interaction. <i>Materials Science Forum</i> , <b>2002</b> , 389-393, 501-504	0.4	8
296	Theoretical Investigation of an Intrinsic Defect in SiC. <i>Materials Science Forum</i> , <b>2002</b> , 389-393, 477-480	0.4	8
295	High Growth Rate Epitaxy of Thick 4H-SiC Layers. <i>Materials Science Forum</i> , <b>2000</b> , 338-342, 165-168	0.4	8
294	The Neutral Silicon Vacancy in 6H and 4H SiC. <i>Materials Science Forum</i> , <b>1998</b> , 264-268, 473-476	0.4	8
293	Electron-paramagnetic-resonance studies of defects in electron-irradiated p-type 4H and 6H SiC. <i>Physica B: Condensed Matter</i> , <b>1999</b> , 273-274, 655-658	2.8	8
292	Nitrogen impurity incorporation behavior in a chimney HTCVD process: pressure and temperature dependence. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , <b>1999</b> , 61-62, 151-154	3.1	8
291	Correlation between switching to n-type conductivity and structural defects in highly Mg-doped InN. <i>Applied Physics Letters</i> , <b>2015</b> , 106, 232102	3.4	7
290	Brominated Chemistry for Chemical Vapor Deposition of Electronic Grade SiC. <i>Chemistry of Materials</i> , <b>2015</b> , 27, 793-801	9.6	7
289	Chloride-Based CVD at High Rates of 4H-SiC on On-Axis Si-Face Substrates. <i>Materials Science Forum</i> , <b>2011</b> , 679-680, 59-62	0.4	7
288	Silicon in AlN: shallow donor and DX behaviors. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2011</b> , 8, 2167-2169		7
287	Chloride-Based CVD at High Growth Rates on 3 $\mu$ vicinal Off-Angles SiC Wafers. <i>Materials Science Forum</i> , <b>2010</b> , 645-648, 107-110	0.4	7
286	Growth of Thick 4H-SiC Epitaxial Layers on On-Axis Si-Face Substrates with HCl Addition. <i>Materials Science Forum</i> , <b>2009</b> , 615-617, 93-96	0.4	7
285	Optical Identification of Mo Related Deep Level Defect in 4H and 6H SiC. <i>Materials Science Forum</i> , <b>2009</b> , 615-617, 405-408	0.4	7
284	Bistable defects in low-energy electron irradiated n-type 4H-SiC. <i>Physica Status Solidi - Rapid Research Letters</i> , <b>2010</b> , 4, 227-229	2.5	7

283	Investigation of domain evolution in sublimation epitaxy of SiC. <i>Journal of Crystal Growth</i> , <b>1998</b> , 193, 101-108	1.6	7
282	Effective-mass approximation for shallow donors in uniaxial indirect band-gap crystals and application to 4HSiC. <i>Physical Review B</i> , <b>2006</b> , 73,	3.3	7
281	Anti-site pair in SiC: a model of the DI center. <i>Physica B: Condensed Matter</i> , <b>2003</b> , 340-342, 175-179	2.8	7
280	Comparison of SiC sublimation epitaxial growth in graphite and TaC coated crucibles. <i>Diamond and Related Materials</i> , <b>2003</b> , 12, 1936-1939	3.5	7
279	SiC and III-Nitride Growth in Hot-Wall CVD Reactor. <i>Materials Science Forum</i> , <b>2005</b> , 483-485, 61-66	0.4	7
278	Neutron Irradiation of 4H SiC. <i>Materials Science Forum</i> , <b>2001</b> , 353-356, 555-558	0.4	7
277	Properties of the UD-1 Deep-Level Center in 4H-SiC. <i>Materials Science Forum</i> , <b>2002</b> , 389-393, 505-508	0.4	7
276	Structural defects and deep-level centers in 4H-SiC epilayers grown by sublimational epitaxy in vacuum. <i>Semiconductors</i> , <b>2000</b> , 34, 1133-1136	0.7	7
275	Excitation properties of hydrogen-related photoluminescence in 6HSiC. <i>Physical Review B</i> , <b>2000</b> , 62, 7162-7168	3.3	7
274	Morphology Control for Growth of Thick Epitaxial 4H SiC Layers. <i>Materials Science Forum</i> , <b>2000</b> , 338-342, 137-140	0.4	7
273	Vacancies and their Complexes with H in SiC. <i>Materials Science Forum</i> , <b>2000</b> , 338-342, 817-820	0.4	7
272	Metastability of a Hydrogen-related Defect in 6H-SiC. <i>Materials Science Forum</i> , <b>2000</b> , 338-342, 651-654	0.4	7
271	Thickness Contour Mapping of SiC Epi-Films on SiC Substrates. <i>Materials Science Forum</i> , <b>1998</b> , 264-268, 645-648	0.4	7
270	Structural investigation of SiC epitaxial layers grown under microgravity and on-ground conditions. <i>Thin Solid Films</i> , <b>1999</b> , 357, 137-143	2.2	7
269	Photo-admittance spectroscopy. <i>Solid State Communications</i> , <b>1983</b> , 46, 895-897	1.6	7
268	Deep levels in as-grown and electron-irradiated n-type GaN studied by deep level transient spectroscopy and minority carrier transient spectroscopy. <i>Journal of Applied Physics</i> , <b>2016</b> , 119, 095707	2.5	7
267	The origin of a peak in the reststrahlen region of SiC. <i>Physica B: Condensed Matter</i> , <b>2012</b> , 407, 1525-1528	2.8	6
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265	Assessment of H-intercalated graphene for microwave FETs through material characterization and electron transport studies. <i>Carbon</i> , <b>2015</b> , 81, 96-104	10.4	6
264	Fast Growth Rate Epitaxy on 4° Off-Cut 4-Inch Diameter 4H-SiC Wafers. <i>Materials Science Forum</i> , <b>2014</b> , 778-780, 179-182	0.4	6
263	Surface Preparation of 4° Off-Axis 4H-SiC Substrate for Epitaxial Growth. <i>Materials Science Forum</i> , <b>2013</b> , 740-742, 225-228	0.4	6
262	Defects in 4H-SiC Layers Grown by Chloride-Based Epitaxy. <i>Materials Science Forum</i> , <b>2009</b> , 615-617, 373-376	0.4	6
261	The Silicon Vacancy in SiC. <i>Materials Science Forum</i> , <b>2009</b> , 615-617, 347-352	0.4	6
260	Chloride Based CVD of 3C-SiC on (0001) SiC Substrates. <i>Materials Science Forum</i> , <b>2011</b> , 679-680, 75-78	0.4	6
259	Carrot Defect Control in Chloride-Based CVD through Optimized Ramp up Conditions. <i>Materials Science Forum</i> , <b>2012</b> , 717-720, 109-112	0.4	6
258	High quality 4H-SiC grown on various substrate orientations. <i>Diamond and Related Materials</i> , <b>1997</b> , 6, 1289-1292	3.5	6
257	Divacancy Model for P6/P7 Centers in 4H- and 6H-SiC. <i>Materials Science Forum</i> , <b>2006</b> , 527-529, 527-530	0.4	6
256	Properties of Thick n- and p-Type Epitaxial Layers of 4H-SiC Grown by Hot-Wall CVD on Off- and On-Axis Substrates. <i>Materials Science Forum</i> , <b>2006</b> , 527-529, 183-186	0.4	6
255	Electron Paramagnetic Resonance Study of the HE14/SI5 Center in 4H-SiC. <i>Materials Science Forum</i> , <b>2006</b> , 527-529, 543-546	0.4	6
254	4H-SiC Epitaxial Layers Grown on On-Axis Si-Face Substrate. <i>Materials Science Forum</i> , <b>2007</b> , 556-557, 53-56	0.4	6
253	Growth of High Quality p-Type 4H-SiC Substrates by HTCVD. <i>Materials Science Forum</i> , <b>2003</b> , 433-436, 21-24	0.4	6
252	The 3838 $\phi$ photoluminescence line in 4H-SiC. <i>Journal of Applied Physics</i> , <b>2003</b> , 94, 2901-2906	2.5	6
251	Presence of Hydrogen in SiC. <i>Materials Science Forum</i> , <b>2001</b> , 353-356, 373-376	0.4	6
250	Incorporation of Hydrogen (1H and 2H) into 4H-SiC during Epitaxial Growth. <i>Materials Science Forum</i> , <b>2002</b> , 389-393, 565-568	0.4	6
249	The Carbon Vacancy Pair in 4H and 6H SiC. <i>Materials Science Forum</i> , <b>2000</b> , 338-342, 821-824	0.4	6
248	Designing, Physical Simulation and Fabrication of High-Voltage (3.85 kV) 4H-SiC Schottky Rectifiers Processed on Hot-Wall and Chimney CVD Films. <i>Materials Science Forum</i> , <b>2000</b> , 338-342, 1171-1174	0.4	6

247	Cathodoluminescence of Defect Regions in SiC Epi-Films. <i>Materials Science Forum</i> , <b>1998</b> , 264-268, 653-656	0.4	6
246	Optically Detected Magnetic Resonance Studies of Non-Radiative Recombination Centres in 6H SiC. <i>Materials Science Forum</i> , <b>1998</b> , 264-268, 599-602	0.4	6
245	Zeeman spectroscopy of the D1 bound exciton in 3C and 4H SiC. <i>Physica B: Condensed Matter</i> , <b>1999</b> , 273-274, 677-680	2.8	6
244	Shallow excited states of deep luminescent centers in silicon. <i>Solid State Communications</i> , <b>1995</b> , 93, 415-418	1.8	6
243	Metastable chalcogen-related luminescent centers in silicon. <i>Physical Review B</i> , <b>1994</b> , 49, 1662-1667	3.3	6
242	S-Cu-related metastable complex defect in Si by optical detection of magnetic resonance. <i>Physical Review B</i> , <b>1994</b> , 50, 7365-7370	3.3	6
241	AlGaN/GaN high electron mobility transistors with intentionally doped GaN buffer using propane as carbon precursor. <i>Japanese Journal of Applied Physics</i> , <b>2016</b> , 55, 05FK02	1.4	6
240	The Role of Chlorine during High Growth Rate Epitaxy. <i>Materials Science Forum</i> , <b>2015</b> , 821-823, 141-144	0.4	5
239	ZrB <sub>2</sub> thin films deposited on GaN(0001) by magnetron sputtering from a ZrB <sub>2</sub> target. <i>Journal of Crystal Growth</i> , <b>2016</b> , 453, 71-76	1.6	5
238	Extraction and scattering analyses of 2D and bulk carriers in epitaxial graphene-on-SiC structure. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2014</b> , 63, 87-92	3	5
237	The charged exciton in an InGaN quantum dot on a GaN pyramid. <i>Applied Physics Letters</i> , <b>2013</b> , 103, 013109	1.9	5
236	Matching precursor kinetics to afford a more robust CVD chemistry: a case study of the C chemistry for silicon carbide using SiF <sub>4</sub> as Si precursor. <i>Journal of Materials Chemistry C</i> , <b>2017</b> , 5, 5818-5823	7.1	5
235	Optical properties and Zeeman spectroscopy of niobium in silicon carbide. <i>Physical Review B</i> , <b>2015</b> , 92,	3.3	5
234	Shallow donor in natural MoS <sub>2</sub> . <i>Physica Status Solidi - Rapid Research Letters</i> , <b>2015</b> , 9, 707-710	2.5	5
233	Characterization of the nitrogen split interstitial defect in wurtzite aluminum nitride using density functional theory. <i>Journal of Applied Physics</i> , <b>2014</b> , 116, 113702	2.5	5
232	Influence of Large-Aspect-Ratio Surface Roughness on Electrical Characteristics of AlGaN/AlN/GaN HFETs. <i>IEEE Transactions on Device and Materials Reliability</i> , <b>2012</b> , 12, 538-546	1.6	5
231	High Growth Rate with Reduced Surface Roughness during On-Axis Homoepitaxial Growth of 4H-SiC. <i>Materials Science Forum</i> , <b>2011</b> , 679-680, 115-118	0.4	5
230	Single Crystal and Polycrystalline 3C-SiC for MEMS Applications. <i>Materials Science Forum</i> , <b>2009</b> , 615-617, 625-628	0.4	5

229	Ionization energy of the phosphorus donor in 3C-SiC from the donor-acceptor pair emission. <i>Journal of Applied Physics</i> , <b>2010</b> , 108, 063532	2.5	5
228	Magnetic characterization of conductance electrons in GaN. <i>Physica Status Solidi (B): Basic Research</i> , <b>2010</b> , 247, 1728-1731	1.3	5
227	A Deep Photoluminescence Band in 4H-SiC Related to the Silicon Vacancy. <i>Materials Science Forum</i> , <b>1997</b> , 258-263, 685-690	0.4	5
226	Very High Growth Rate of 4H-SiC Using MTS as Chloride-Based Precursor. <i>Materials Science Forum</i> , <b>2008</b> , 600-603, 115-118	0.4	5
225	Epitaxial growth of thin 4H-SiC layers with uniform doping depth profile. <i>Thin Solid Films</i> , <b>2006</b> , 515, 460-463	1.6	5
224	Study of nitrogen, aluminium and boron incorporation in SiC layers grown by sublimation epitaxy. <i>Journal of Crystal Growth</i> , <b>2002</b> , 237-239, 1230-1234	1.6	5
223	Investigation of thermal properties in fabricated 4H-SiC high power bipolar transistors. <i>Solid-State Electronics</i> , <b>2003</b> , 47, 639-644	1.7	5
222	Electron Paramagnetic Resonance of Shallow Phosphorous Centers in 4H- and 6H-SiC. <i>Materials Science Forum</i> , <b>2005</b> , 483-485, 515-518	0.4	5
221	Theoretical Investigations of Complexes of p-Type Dopants and Carbon Interstitial in SiC: Bistable, Negative-U Defects. <i>Materials Science Forum</i> , <b>2005</b> , 483-485, 519-522	0.4	5
220	Effective-Mass Theory of Shallow Donors in 4H-SiC. <i>Materials Science Forum</i> , <b>2005</b> , 483-485, 511-514	0.4	5
219	Aluminum Doping of Epitaxial Silicon Carbide Grown by Hot-Wall CVD; Effect of Process Parameters. <i>Materials Science Forum</i> , <b>2002</b> , 389-393, 203-206	0.4	5
218	Lateral Enlargement of Silicon Carbide Crystals. <i>Materials Science Forum</i> , <b>2002</b> , 389-393, 39-42	0.4	5
217	Structural Defects in Electrically Degraded 4H-SiC PIN Diodes. <i>Materials Science Forum</i> , <b>2002</b> , 389-393, 423-426	0.4	5
216	Photoluminescence Study of CVD Layers Highly Doped with Nitrogen. <i>Materials Science Forum</i> , <b>2000</b> , 338-342, 619-622	0.4	5
215	Reactive UHV Sputtering and Structural Characterization of Epitaxial AlN/6H-SiC(0001) Thin Films. <i>Materials Science Forum</i> , <b>1998</b> , 264-268, 1225-1228	0.4	5
214	Observation of Metastable Defect in Electron Irradiated 6H-SiC. <i>Materials Science Forum</i> , <b>1998</b> , 264-268, 561-564	0.4	5
213	Silicon carbide grown by liquid phase epitaxy in microgravity. <i>Journal of Materials Research</i> , <b>1998</b> , 13, 1812-1815	2.5	5
212	Configuration transformation of metastable defects in 6H-SiC. <i>Semiconductor Science and Technology</i> , <b>1999</b> , 14, 251-256	1.8	5



211	Photoluminescence of 4H-SiC: some remarks. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , <b>1999</b> , 61-62, 234-238	3.1	5
210	GaAs Low Temperature Fusion Bonding. <i>Journal of the Electrochemical Society</i> , <b>1994</b> , 141, 3242-3245	3.9	5
209	Development of an all-SiC neuronal interface device. <i>MRS Advances</i> , <b>2016</b> , 1, 3679-3684	0.7	5
208	Wafer Scale On-Axis Homoepitaxial Growth of 4H-SiC(0001) for High-Power Devices: Influence of Different Gas Phase Chemistries and Growth Rate Limitations. <i>Crystal Growth and Design</i> , <b>2019</b> , 19, 3288-3297	3.5	4
207	SiC Substrate effects on electron transport in the epitaxial graphene layer. <i>Electronic Materials Letters</i> , <b>2014</b> , 10, 387-391	2.9	4
206	Thermal conductivity of isotopically enriched silicon carbide <b>2013</b> ,		4
205	Hydrogen at zinc vacancy of ZnO: An EPR and ESEEM study <b>2014</b> ,		4
204	Effects of phosphorous-doping and high temperature annealing on CVD grown 3C-SiC. <i>Nuclear Engineering and Design</i> , <b>2012</b> , 251, 191-202	1.8	4
203	Influence of Growth Temperature on Carrier Lifetime in 4H-SiC Epilayers. <i>Materials Science Forum</i> , <b>2013</b> , 740-742, 637-640	0.4	4
202	Large area mapping of the alloy composition of Al <sub>x</sub> Ga <sub>1-x</sub> N using infrared reflectivity. <i>Physica Status Solidi - Rapid Research Letters</i> , <b>2009</b> , 3, 145-147	2.5	4
201	The Effect of Growth Conditions on Carrier Lifetime in N-Type 4H-SiC Epitaxial Layers. <i>Materials Science Forum</i> , <b>2012</b> , 717-720, 161-164	0.4	4
200	Radiation-induced defects in GaN. <i>Physica Scripta</i> , <b>2010</b> , T141, 014015	2.6	4
199	Effects of microwave fields on recombination processes in 4H and 6H SiC. <i>Journal of Applied Physics</i> , <b>1997</b> , 81, 1929-1932	2.5	4
198	Growth of 4H-SiC from liquid phase. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , <b>1997</b> , 46, 329-332	3.1	4
197	The D1 Exciton in 4H-SiC. <i>Physica Status Solidi (B): Basic Research</i> , <b>1998</b> , 210, 337-340	1.3	4
196	Intrinsic Defects in HPSI 6H-SiC: an EPR Study. <i>Materials Science Forum</i> , <b>2008</b> , 600-603, 381-384	0.4	4
195	Common point defects in as-grown ZnO substrates studied by optical detection of magnetic resonance. <i>Journal of Crystal Growth</i> , <b>2008</b> , 310, 1006-1009	1.6	4
194	Identification of divacancies in 4H-SiC. <i>Physica B: Condensed Matter</i> , <b>2006</b> , 376-377, 334-337	2.8	4

193	Nitrogen Delta Doping in 4H-SiC Epilayers. <i>Materials Science Forum</i> , <b>2003</b> , 433-436, 153-156	0.4	4
192	Performance of III-nitride epitaxy in a low V-to-III gas-flow ratio range under nitrogen ambient in a hot-wall MOCVD system. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2005</b> , 2, 960-963		4
191	Recombination Enhanced Defect Annealing in 4H-SiC. <i>Materials Science Forum</i> , <b>2005</b> , 483-485, 369-372	0.4	4
190	Behavior of background impurities in thick 4H-SiC epitaxial layers. <i>Applied Surface Science</i> , <b>2001</b> , 184, 242-246	6.7	4
189	High-Resolution XRD Evaluation of Thick 4H-SiC Epitaxial Layers. <i>Materials Science Forum</i> , <b>2001</b> , 353-356, 291-294	0.4	4
188	Excitation spectra of nitrogen bound excitons in 4H- and 6H-SiC. <i>Journal of Applied Physics</i> , <b>2002</b> , 91, 2028-2032	2.5	4
187	Investigation of Thermal Properties in Fabricated 4H-SiC High-Power Bipolar Transistors. <i>Materials Science Forum</i> , <b>2002</b> , 389-393, 1337-1340	0.4	4
186	The Effect of Hydrogen Diffusion in p- and n-Type SiC Schottky Diodes at High Temperatures. <i>Materials Science Forum</i> , <b>2002</b> , 389-393, 1419-1422	0.4	4
185	Characteristics of Boron in 4H-SiC Layers Produced by High-Temperature Techniques. <i>Materials Science Forum</i> , <b>2002</b> , 389-393, 259-262	0.4	4
184	Power Schottky and p-n Diodes on SiC Epi-Wafers with Reduced Micropipe Density. <i>Materials Science Forum</i> , <b>2002</b> , 389-393, 1173-1176	0.4	4
183	Photoconductivity of Lightly-Doped and Semi-Insulating 4H-SiC and the Free Exciton Binding Energy. <i>Materials Science Forum</i> , <b>2002</b> , 389-393, 613-616	0.4	4
182	Pseudo-Donors in SiC. <i>Materials Science Forum</i> , <b>2000</b> , 338-342, 647-650	0.4	4
181	Time Resolved PL Study of Multi Bound Excitons in 3C SiC. <i>Materials Science Forum</i> , <b>1998</b> , 264-268, 485-488	0.4	4
180	Chromium in 4H and 6H SiC: Photoluminescence and Zeeman Studies. <i>Materials Science Forum</i> , <b>1998</b> , 264-268, 603-606	0.4	4
179	Purity and surface structure of thick 6H and 4H SiC layers grown by sublimation epitaxy. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , <b>1999</b> , 61-62, 147-150	3.1	4
178	Photoluminescence excitation spectra of the free exciton emission in 6H-SiC. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , <b>1999</b> , 61-62, 265-269	3.1	4
177	Direct determination of the electron-electron-hole Auger threshold energy in silicon. <i>Physical Review Letters</i> , <b>1994</b> , 73, 3258-3261	7.4	4
176	Electron capture cross-section in copper doped CdS. <i>Solid State Communications</i> , <b>1980</b> , 35, 727-728	1.6	4

175	The localisation of donor electrons in multivalley split 1s states for group V and VI donors in silicon. <i>Journal of Physics C: Solid State Physics</i> , <b>1982</b> , 15, 5791-5797		4
174	Characterization of InGaN/GaN quantum well growth using monochromated valence electron energy loss spectroscopy. <i>Journal of Applied Physics</i> , <b>2014</b> , 115, 034302	2.5	3
173	Comparison of Carrier Lifetime Measurements and Mapping in 4H SiC Using Time Resolved Photoluminescence and $\mu$ PCD. <i>Materials Science Forum</i> , <b>2014</b> , 778-780, 301-304	0.4	3
172	Finding the Optimum Chloride-Based Chemistry for Chemical Vapor Deposition of SiC. <i>ECS Journal of Solid State Science and Technology</i> , <b>2014</b> , 3, P320-P323	2	3
171	The effect of grain size and phosphorous-doping of polycrystalline 3C SiC on infrared reflectance spectra. <i>Journal of Nuclear Materials</i> , <b>2012</b> , 422, 103-108	3.3	3
170	In-grown stacking-faults in 4H-SiC epilayers grown on 2° off-cut substrates. <i>Physica Status Solidi (B): Basic Research</i> , <b>2015</b> , 252, 1319-1324	1.3	3
169	Improved Epilayer Surface Morphology on 2° Off-Cut 4H-SiC Substrates. <i>Materials Science Forum</i> , <b>2014</b> , 778-780, 206-209	0.4	3
168	On-Axis Homoepitaxial Growth of 4H-SiC PiN Structure for High Power Applications. <i>Materials Science Forum</i> , <b>2013</b> , 740-742, 173-176	0.4	3
167	Concentrated Chloride-Based Epitaxial Growth of 4H-SiC. <i>Materials Science Forum</i> , <b>2010</b> , 645-648, 95-98	0.4	3
166	On-Axis Homoepitaxy on Full 2° 4H-SiC Wafer for High Power Applications. <i>Materials Science Forum</i> , <b>2009</b> , 615-617, 133-136	0.4	3
165	Observation of Bistable Defects in Electron Irradiated N-Type 4H-SiC. <i>Materials Science Forum</i> , <b>2011</b> , 679-680, 249-252	0.4	3
164	Identification of Niobium in 4H-SiC by EPR and Ab Initio Studies. <i>Materials Science Forum</i> , <b>2012</b> , 717-720, 217-220	0.4	3
163	Defect mapping in 4H-SiC wafers. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , <b>1997</b> , 46, 287-290	3.1	3
162	A surface study of wet etched AlGaN epilayers grown by hot-wall MOCVD. <i>Journal of Crystal Growth</i> , <b>2007</b> , 300, 242-245	1.6	3
161	Signature of the Negative Carbon Vacancy-Antisite Complex. <i>Materials Science Forum</i> , <b>2006</b> , 527-529, 539-542	0.4	3
160	Intrinsic Defects in Semi-Insulating SiC: Deep Levels and their Roles in Carrier Compensation. <i>Materials Science Forum</i> , <b>2007</b> , 556-557, 465-468	0.4	3
159	Boron-related luminescence in SiC. <i>Physica B: Condensed Matter</i> , <b>2003</b> , 340-342, 141-145	2.8	3
158	Structural impact of LPE buffer layer on sublimation grown 4H SiC epilayers. <i>Journal of Crystal Growth</i> , <b>2003</b> , 256, 276-282	1.6	3

157	The Effect of Thermal Gradients on SiC Wafers. <i>Materials Science Forum</i> , <b>2003</b> , 433-436, 193-196	0.4	3
156	A Comparison of MESFETs on Different 4H-Silicon Carbide Semi-Insulating Substrates. <i>Materials Science Forum</i> , <b>2003</b> , 433-436, 737-740	0.4	3
155	Properties of Different Stacking Faults that Cause Degradation in SiC PiN Diodes. <i>Materials Science Forum</i> , <b>2003</b> , 433-436, 913-916	0.4	3
154	As-Grown and Process-Induced Intrinsic Deep-Level Luminescence in 4H-SiC. <i>Materials Science Forum</i> , <b>2001</b> , 353-356, 365-368	0.4	3
153	Impact of the Initial Surface Conditions on Defect Appearance in 4H-SiC Epilayers. <i>Materials Science Forum</i> , <b>2002</b> , 389-393, 283-286	0.4	3
152	Growth Characteristics of SiC in a Hot-Wall CVD Reactor with Rotation. <i>Materials Science Forum</i> , <b>2002</b> , 389-393, 191-194	0.4	3
151	Impurity-Controlled Dopant Activation - The Role of Hydrogen in p-Type Doping of SiC. <i>Materials Science Forum</i> , <b>2002</b> , 389-393, 561-564	0.4	3
150	Predicting Growth Rates of SiC Epitaxial Layers Grown by Hot-Wall Chemical Vapor Deposition. <i>Materials Science Forum</i> , <b>2002</b> , 389-393, 219-222	0.4	3
149	Influence of Trenching Effect on the Characteristics of Buried-Gate SiC Junction Field-Effect Transistors. <i>Materials Science Forum</i> , <b>2002</b> , 389-393, 1235-1238	0.4	3
148	Photoluminescence upconversion in 4H-SiC. <i>Applied Physics Letters</i> , <b>2002</b> , 81, 2547-2549	3.4	3
147	Some Aspects of the Photoluminescence and Raman Spectroscopy of (10-10)- and (11-20)-Oriented 4H and 6H Silicon Carbide. <i>Materials Science Forum</i> , <b>1998</b> , 264-268, 469-472	0.4	3
146	Kinetics and morphological stability in sublimation growth of 6H and 4H SiC epitaxial layers. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , <b>1999</b> , 61-62, 161-164 <sup>3.1</sup>	3.1	3
145	Domain misorientation in sublimation grown 4H SiC epitaxial layers. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , <b>1999</b> , 61-62, 168-171	3.1	3
144	Microhardness of 6H-SiC Epitaxial Layers Grown by Sublimation. <i>Crystal Research and Technology</i> , <b>1999</b> , 34, 943-947	1.3	3
143	XPS Study of Ni Layers Deposited on 6H-SiC. <i>Materials Science Forum</i> , <b>1996</b> , 207-209, 293-296	0.4	3
142	The Configurational Change of a Metastable S-Cu Defect in Silicon. <i>Materials Science Forum</i> , <b>1993</b> , 143-147, 1179-1184	0.4	3
141	Micro-scribes in semi-insulating GaAs studied by cross-sectional transmission electron microscopy. <i>Journal of Crystal Growth</i> , <b>1994</b> , 143, 22-28	1.6	3
140	New photoluminescence lines in selenium-doped silicon. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , <b>1989</b> , 4, 261-264	3.1	3

139	Electronic properties of defects in high-fluence electron-irradiated bulk GaN. <i>Physica Status Solidi (B): Basic Research</i> , <b>2016</b> , 253, 521-526	1.3	3
138	Oxidation Induced ON1, ON2a/b Defects in 4H-SiC Characterized by DLTS. <i>Materials Science Forum</i> , <b>2014</b> , 778-780, 281-284	0.4	2
137	Optical characterization of individual quantum dots. <i>Physica B: Condensed Matter</i> , <b>2012</b> , 407, 1472-1475	2.8	2
136	Simulation of Gas-Phase Chemistry for Selected Carbon Precursors in Epitaxial Growth of SiC. <i>Materials Science Forum</i> , <b>2013</b> , 740-742, 213-216	0.4	2
135	Properties of GaN layers grown on N-face free-standing GaN substrates. <i>Journal of Crystal Growth</i> , <b>2015</b> , 413, 81-85	1.6	2
134	Silicon and Oxygen in High-Al-Content AlGaIn: Incorporation Kinetics and Electron Paramagnetic Resonance Study. <i>Solid State Phenomena</i> , <b>2013</b> , 205-206, 441-445	0.4	2
133	Metastable Defects in Low-Energy Electron Irradiated n-Type 4H-SiC. <i>Materials Science Forum</i> , <b>2010</b> , 645-648, 435-438	0.4	2
132	Chloride-based CVD of 3C-SiC Epitaxial Layers on On-axis 6H (0001) SiC Substrates <b>2010</b> ,		2
131	Defects Introduced by Electron-Irradiation at Low Temperatures in SiC. <i>Materials Science Forum</i> , <b>2009</b> , 615-617, 377-380	0.4	2
130	Chloride-Based SiC Epitaxial Growth. <i>Materials Science Forum</i> , <b>2009</b> , 615-617, 89-92	0.4	2
129	Chloride-Based CVD of 4H-SiC at High Growth Rates on Substrates with Different Off-Angles. <i>Materials Science Forum</i> , <b>2012</b> , 717-720, 113-116	0.4	2
128	CVD Heteroepitaxial Growth of 3C-SiC on 4H-SiC (0001) Substrates. <i>Materials Science Forum</i> , <b>2012</b> , 717-720, 189-192	0.4	2
127	CVD Growth of 3C-SiC on 4H-SiC Substrate. <i>Materials Science Forum</i> , <b>2012</b> , 711, 16-21	0.4	2
126	High-Resolution Time-Resolved Carrier Lifetime and Photoluminescence Mapping of 4H-SiC Epilayers. <i>Materials Science Forum</i> , <b>2012</b> , 717-720, 293-296	0.4	2
125	Transition Metal Defects in Cubic and Hexagonal Polytypes of SiC: Site Selection, Magnetic and Optical Properties from Ab Initio Calculations. <i>Materials Science Forum</i> , <b>2012</b> , 717-720, 205-210	0.4	2
124	Defects in low-energy electron-irradiated n-type 4H-SiC. <i>Physica Scripta</i> , <b>2010</b> , T141, 014006	2.6	2
123	Optically detected magnetic resonance studies of defects in 3C SiC epitaxial layers. <i>Diamond and Related Materials</i> , <b>1997</b> , 6, 1381-1384	3.5	2
122	Point Defects in SiC. <i>Materials Research Society Symposia Proceedings</i> , <b>2008</b> , 1069, 1		2

121	Magnetic resonance studies of defects in electron-irradiated ZnO substrates. <i>Physica B: Condensed Matter</i> , <b>2007</b> , 401-402, 507-510	2.8	2
120	Titanium related luminescence in SiC. <i>Superlattices and Microstructures</i> , <b>2006</b> , 40, 328-331	2.8	2
119	In-Diffusion, Trapping and Out-Diffusion of Deuterium in 4H-SiC Substrates. <i>Materials Science Forum</i> , <b>2006</b> , 527-529, 637-640	0.4	2
118	Characterization of Semi-insulating SiC. <i>Materials Research Society Symposia Proceedings</i> , <b>2006</b> , 911, 3		2
117	Influence of Cooling Rate after High Temperature Annealing on Deep Levels in High-Purity Semi-Insulating 4H-SiC. <i>Materials Science Forum</i> , <b>2007</b> , 556-557, 371-374	0.4	2
116	Growth and Photoluminescence Study of Aluminium Doped SiC Epitaxial Layers. <i>Materials Science Forum</i> , <b>2007</b> , 556-557, 97-100	0.4	2
115	Thick Epilayer for Power Devices. <i>Materials Science Forum</i> , <b>2007</b> , 556-557, 47-52	0.4	2
114	Deep Acceptor Levels of the Carbon Vacancy-Carbon Antisite Pairs in 4H-SiC. <i>Materials Science Forum</i> , <b>2007</b> , 556-557, 449-452	0.4	2
113	Phosphorus-related luminescence in SiC. <i>Physica Scripta</i> , <b>2006</b> , T126, 45-49	2.6	2
112	4H-SiC Power Schottky Diodes. On the Way to Solve the Size Limiting Issues. <i>Materials Science Forum</i> , <b>2004</b> , 457-460, 985-988	0.4	2
111	Lateral enlargement of silicon carbide crystals. <i>Journal of Crystal Growth</i> , <b>2004</b> , 270, 7-14	1.6	2
110	Kinetics of residual doping in 4H-SiC epitaxial layers grown in vacuum. <i>Journal of Crystal Growth</i> , <b>2002</b> , 240, 501-507	1.6	2
109	Correlation between Electrical and Optical Mapping of Boron Related Complexes in 4H-SiC. <i>Materials Science Forum</i> , <b>2003</b> , 433-436, 423-426	0.4	2
108	Orientation-Dependent Defect Formation in Silicon Carbide Epitaxial Layers. <i>Materials Science Forum</i> , <b>2003</b> , 433-436, 281-284	0.4	2
107	Implementation of Hot-Wall MOCVD to the Growth of High-Quality GaN on SiC. <i>Materials Science Forum</i> , <b>2003</b> , 433-436, 991-994	0.4	2
106	Doping-Related Strain in n-Doped 4H-SiC Crystals. <i>Materials Science Forum</i> , <b>2003</b> , 433-436, 269-272	0.4	2
105	Time-Resolved Photoluminescence of Deep Centers in Semi-Insulating 4H-SiC. <i>Materials Science Forum</i> , <b>2003</b> , 433-436, 301-304	0.4	2
104	Growth of Homoepitaxial Films on 4H-SiC(11-20) and 8° Off-Axis 4H-SiC(0001) Substrates and their Characterization. <i>Materials Science Forum</i> , <b>2004</b> , 457-460, 221-224	0.4	2

103	Observation of Vacancy Clusters in HTCVD Grown SiC. <i>Materials Science Forum</i> , <b>2005</b> , 483-485, 469-472	0.4	2
102	Nonequilibrium Carrier Diffusion and Recombination in Heavily-Doped and Semi-Insulating Bulk HTCVD Grown 4H-SiC Crystals. <i>Materials Science Forum</i> , <b>2005</b> , 483-485, 409-412	0.4	2
101	Enlarging the Usable Growth Area in a Hot-Wall Silicon Carbide CVD Reactor by Using Simulation. <i>Materials Science Forum</i> , <b>2001</b> , 353-356, 99-102	0.4	2
100	Influence of Epitaxial Layer on SiC Schottky Diode Gas Sensors Operated under High-Temperature Conditions. <i>Materials Science Forum</i> , <b>2002</b> , 389-393, 1423-1426	0.4	2
99	Characterization of Anisotropic Step-bunching on as-grown SiC Surfaces. <i>Materials Science Forum</i> , <b>2000</b> , 338-342, 375-378	0.4	2
98	Vanadium-related Center in 4H Silicon Carbide. <i>Materials Science Forum</i> , <b>2000</b> , 338-342, 631-634	0.4	2
97	Electroluminescence From Implanted and Epitaxially Grown pn-Diodes. <i>Materials Science Forum</i> , <b>2000</b> , 338-342, 687-690	0.4	2
96	Stress related morphological defects in SiC epitaxial layers. <i>Diamond and Related Materials</i> , <b>2001</b> , 10, 1246-1250	3.5	2
95	Near Band-Gap Emission in V-Implanted and Annealed 4H-SiC. <i>Materials Science Forum</i> , <b>1998</b> , 264-268, 497-500	0.4	2
94	Structural analysis of 4H-SiC layers grown on 6H-SiC and 15R-SiC substrates. <i>Journal of Crystal Growth</i> , <b>1995</b> , 152, 292-299	1.6	2
93	Temperature and doping dependence of the photon recycling effect in GaAs/AlGaAs heterostructures. <i>Journal of Applied Physics</i> , <b>1995</b> , 77, 4611-4615	2.5	2
92	A Metastable Selenium-Related Center in Silicon. <i>Materials Science Forum</i> , <b>1993</b> , 143-147, 159-164	0.4	2
91	Fano resonances in sulfur, selenium and tellurium doped silicon. <i>Physica B: Physics of Condensed Matter &amp; C: Atomic, Molecular and Plasma Physics, Optics</i> , <b>1983</b> , 117-118, 125-127		2
90	Scalable Quantum Photonics with Single Color Centers in Silicon Carbide <b>2017</b> ,		2
89	Chloride-based SiC growth on a-axis 4H-SiC substrates. <i>Physica B: Condensed Matter</i> , <b>2016</b> , 480, 23-25	2.8	1
88	Influence of n-Type Doping Levels on Carrier Lifetime in 4H-SiC Epitaxial Layers. <i>Materials Science Forum</i> , <b>2017</b> , 897, 238-241	0.4	1
87	Defects in silicon carbide grown by fluorinated chemical vapor deposition chemistry. <i>Physica B: Condensed Matter</i> , <b>2018</b> , 535, 44-49	2.8	1
86	Carrier Mobility as a Function of Temperature in as-Grown and H-Intercalated Epitaxial Graphenes on 4H-SiC. <i>Materials Science Forum</i> , <b>2014</b> , 778-780, 1146-1149	0.4	1

85	Structural Investigation of Heteroepitaxial 3C-SiC Grown on 4H-SiC Substrates. <i>Materials Science Forum</i> , <b>2013</b> , 740-742, 319-322	0.4	1
84	Homo-Epitaxial Growth on Low-Angle Off Cut 4H-SiC Substrate. <i>Materials Science Forum</i> , <b>2014</b> , 778-780, 131-134	0.4	1
83	Revisiting the Thermochemical Database of Si-C-H System Related to SiC CVD Modeling. <i>Materials Science Forum</i> , <b>2014</b> , 778-780, 175-178	0.4	1
82	Theoretical Investigation of the Single Photon Emitter Carbon Antisite-Vacancy Pair in 4H-SiC. <i>Materials Science Forum</i> , <b>2014</b> , 778-780, 495-498	0.4	1
81	Optical Properties of the Niobium Centre in 4H, 6H, and 15R SiC. <i>Materials Science Forum</i> , <b>2013</b> , 740-742, 405-408	0.4	1
80	Surface Evolution of 4H-SiC(0001) during In Situ Surface Preparation and its Influence on Graphene Properties. <i>Materials Science Forum</i> , <b>2013</b> , 740-742, 157-160	0.4	1
79	Photoluminescence of 8H-SiC. <i>Materials Science Forum</i> , <b>2013</b> , 740-742, 347-350	0.4	1
78	The Carbon Vacancy Related E14 Defect in 4H-SiC. <i>Materials Science Forum</i> , <b>2010</b> , 645-648, 399-402	0.4	1
77	Micro-Raman spectroscopy as a voltage probe in AlGaIn/GaN heterostructure devices: Determination of buffer resistances. <i>Solid-State Electronics</i> , <b>2011</b> , 55, 5-7	1.7	1
76	Radial Variation of Measured Carrier Lifetimes in Epitaxial Layers Grown with Wafer Rotation. <i>Materials Science Forum</i> , <b>2012</b> , 717-720, 289-292	0.4	1
75	Investigation of Intrinsic Carbon-Related Defects in 4H-SiC by Selective-Excitation Photoluminescence Spectroscopy. <i>Materials Science Forum</i> , <b>2012</b> , 717-720, 259-262	0.4	1
74	Electrical and Optical Properties of High-Purity Epilayers Grown by the Low-Temperature Chloro-Carbon Growth Method. <i>Materials Science Forum</i> , <b>2012</b> , 717-720, 129-132	0.4	1
73	Influence of Growth Mechanism on Carrier Lifetime in On-Axis Homoepitaxial Layers of 4H-SiC. <i>Materials Science Forum</i> , <b>2012</b> , 717-720, 157-160	0.4	1
72	Titanium Related Luminescence in SiC. <i>Materials Science Forum</i> , <b>2008</b> , 600-603, 461-464	0.4	1
71	Improved SiC Epitaxial Material for Bipolar Applications. <i>Materials Research Society Symposia Proceedings</i> , <b>2008</b> , 1069, 1		1
70	Wave-Function Symmetry and the Properties of Shallow P Donors in 4H SiC. <i>Materials Science Forum</i> , <b>2008</b> , 600-603, 445-448	0.4	1
69	Time-resolved photoluminescence properties of AlGaIn/AlN/GaN high electron mobility transistor structures grown on 4H-SiC substrate. <i>Journal of Applied Physics</i> , <b>2008</b> , 104, 113513	2.5	1
68	Clustering of Vacancies in Semi-Insulating SiC Observed with Positron Spectroscopy. <i>Materials Science Forum</i> , <b>2006</b> , 527-529, 575-578	0.4	1



67	Shallow P Donors in 3C-, 4H- and 6H-SiC. <i>Materials Science Forum</i> , <b>2006</b> , 527-529, 593-596	0.4	1
66	Photoluminescence of Phosphorous Doped SiC. <i>Materials Science Forum</i> , <b>2006</b> , 527-529, 589-592	0.4	1
65	Optical Studies of Deep Centers in Semi-Insulating SiC. <i>Materials Science Forum</i> , <b>2006</b> , 527-529, 455-460	0.4	1
64	Hyperfine Interaction of Nitrogen Donor in 4H-SiC Studied by Pulsed-ENDOR. <i>Materials Science Forum</i> , <b>2005</b> , 483-485, 351-354	0.4	1
63	Characteristics of Ni Schottky Contacts on Compensated 4H-SiC Layers. <i>Materials Science Forum</i> , <b>2003</b> , 433-436, 709-712	0.4	1
62	Antisites as Possible Origin of Irradiation Induced Photoluminescence Centers in SiC: A Theoretical Study on Clusters of Antisites and Carbon Interstitials in 4H-SiC. <i>Materials Science Forum</i> , <b>2004</b> , 457-460, 443-448	0.4	1
61	Deep levels in 4H-SiC layers grown by sublimation epitaxy. <i>Optical Materials</i> , <b>2003</b> , 23, 61-64	3.3	1
60	Effect of Ambient on 4H-SiC Bulk Crystals Grown by Sublimation. <i>Materials Science Forum</i> , <b>2003</b> , 433-436, 75-78	0.4	1
59	Donor-Acceptor Pair Luminescence in 4H-SiC Doped with Nitrogen and Aluminum. <i>Materials Science Forum</i> , <b>2003</b> , 433-436, 321-324	0.4	1
58	High quality 6H-SiC (0001) homoepitaxial layers as substrate surface for growth of AlN epitaxial layers. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2005</b> , 2, 2109-2112		1
57	Hot-wall MOCVD grown homoepitaxial GaN layers with intense intrinsic excitonic structure. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2005</b> , 202, 739-743	1.6	1
56	Trapped carrier electroluminescence (TraCE) a novel method for correlating electrical and optical measurements. <i>Physica B: Condensed Matter</i> , <b>2001</b> , 308-310, 1165-1168	2.8	1
55	Epitaxial Growth of 4H-SiC in a Vertical Hot-Wall CVD Reactor: Comparison between Up- and Down-Flow Orientations. <i>Materials Science Forum</i> , <b>2001</b> , 353-356, 91-94	0.4	1
54	Hole and Electron Effective Masses in 6H-SiC Studied by Optically Detected Cyclotron Resonance. <i>Materials Science Forum</i> , <b>2002</b> , 389-393, 525-528	0.4	1
53	Electronic Structure of the UD3 Defect in 4H- and 6H-SiC. <i>Materials Science Forum</i> , <b>2002</b> , 389-393, 509-512	2.4	1
52	Effect of Temperature Treatment on Au/Pd Schottky Contacts to 4H-SiC. <i>Materials Science Forum</i> , <b>2002</b> , 389-393, 929-932	0.4	1
51	Growth of AlN Films by Hot-Wall CVD and Sublimation Techniques: Effect of Growth Cell Pressure. <i>Materials Science Forum</i> , <b>2002</b> , 389-393, 1469-1472	0.4	1
50	Bandstructure and Transport Properties of 4H- and 6H-SiC: Optically Detected Cyclotron Resonance Investigations. <i>Materials Science Forum</i> , <b>2000</b> , 338-342, 559-562	0.4	1

49	Growth of High Quality AlN Epitaxial Films by Hot-Wall Chemical Vapour Deposition. <i>Materials Science Forum</i> , <b>1998</b> , 264-268, 1133-1136	0.4	1
48	Bound Exciton Recombination in Electron Irradiated 4H-SiC. <i>Materials Science Forum</i> , <b>1998</b> , 264-268, 477-480	0.4	1
47	Domain Occurance in SiC Epitaxial Layers Grown by Sublimation. <i>Materials Science Forum</i> , <b>1998</b> , 264-268, 151-154	0.4	1
46	Zeeman spectroscopy of the neutral silicon vacancy in 6H and 4H SiC. <i>Physica B: Condensed Matter</i> , <b>1999</b> , 273-274, 663-666	2.8	1
45	Chen et al. reply. <i>Physical Review Letters</i> , <b>1995</b> , 75, 3963	7.4	1
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